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## **INFORMATION DISCLOSURE** STATEMENT BY APPLICANT

(Use as many sheets as necessary) Sheet

| Complete if Known      |                    |  |  |  |
|------------------------|--------------------|--|--|--|
| Application Number     | Unassigned         |  |  |  |
| Filing Date            | September 12, 2003 |  |  |  |
| First Named Inventor   | Takayuki HISAKA    |  |  |  |
| Group Art Unit         | Unassigned         |  |  |  |
| Examiner Name          | Unassigned         |  |  |  |
| Attorney Docket Number | 402775/AOYAMA      |  |  |  |

|                   |          |                         |                                 | FOREIG       | N PATENT DOCUMENTS            |                        |             |      |
|-------------------|----------|-------------------------|---------------------------------|--------------|-------------------------------|------------------------|-------------|------|
|                   |          | Foreign Patent Document |                                 |              |                               |                        | Translation |      |
| Examiner Initials | Doc. No. | Office                  | Application or<br>Patent Number | Kind<br>Code | Name of Patentee or Applicant | Date of<br>Publication | Yes         | No*+ |
| gr -              | _ A1     | JP                      | 6-244218                        |              | SUMITOMO ELECTRIC IND LTD     | 9/2/1994               |             | X+   |
| cn/               | _ A2     | JP                      | 9-205196                        |              | HITACHI CABLE LTD             | 8/5/1997               |             | X+   |
| cn                | A 3      | JP                      | 9-246528                        |              | HITACHI CABLE LTD             | 9/19/1997              | 1           | X+   |
| Ch/               | Α4       | EPO                     | 0 301 862                       |              | SONY CORP.                    | 1/2/1989               | 1           | X+   |
|                   |          |                         |                                 |              |                               |                        |             |      |
|                   |          |                         |                                 |              |                               |                        |             |      |
|                   |          |                         |                                 |              |                               |                        |             |      |

| OTHER - NON PATENT LITERATURE DOCUMENTS |   |  |      |  |  |
|---|---|--|------|--|--|
| Examiner Initials Doc. No.              |   | Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item                                      |      |  |  |
|   | <ul> <li>(book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number (s),<br/>publisher, city and/or country where published.</li> </ul>  |  | No*+ |  |  |
| à                                       | A 5 C.S. WHELAN et al., "Low Noise In <sub>0.32</sub> (AlGa) <sub>0.68</sub> As/In <sub>0.43</sub> Ga <sub>0.57</sub> As Metamorphic HEMT on GaAs Substrate with 850 mW/mm Output Power Density", IEEE Electron Letters, January 2000, pp. 5-8; Vol. 21, No. 1. |  |      |  |  |
| cu                                      | A 6   | J.C.M. HWANG, "Gradual Degradation Under RF Overdrive Of MESFETs and PHEMTs", GaAs IC Symposium, 1995, pp. 81-84.                                |      |  |  |
| ca                                      | Α7  | Y.A. TKACHENKO et al., "Hot-Electron-Induced Degradation of Metal-Semiconductor Field-Effect Transistors", GaAs IC Symposium, 1994, pp. 259-262. |      |  |  |
| a                                       | A 8   | L. AUCOIN et al., "PHEMT Reliability: The Importance of RF Life Testing", GaAs MANTECH, 1997, pp. 42-45.   |      |  |  |
|   |   |  |      |  |  |

| Examiner Signature |           | Date Considered   |           |
|--------------------|-----------|-------------------|-----------|
| Examiner Signature |           | i Date Considered |           |
| i i                | 1 1/4 ~ 1 | i i               | 11-70-0-0 |
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A concise statement of relevance is being submitted in lieu of a translation. 37 CFR 1.98(a)(3).
 An English-language equivalent/patent/ or an English-language abstract, or an English-language version of the search report or action by a foreign patent office in a counterpart foreign application/indicating the degree of relevance found by the foreign office is being submitted in lieu of a concise explanation of relevance under 37 CFR 1.98(a)(3).